

Pf-2801/ncc/us/mh

ABSTRACT OF THE DISCLOSURE

- A monolithically integrated semiconductor device comprises : a
5 hetero-junction bipolar transistor having at least an electrode contact layer which contacts directly with at least one of collector, base and emitter electrodes ; and at least a passive device having at least a passive device electrode and at least a resistive layer, wherein the electrode contact layer and the resistive layer comprise the same compound semiconductor layer.

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